

**Freescale Semiconductor**  
Technical Data

MRF6P27160H  
Rev. 0, 1/2005

# RF Power Field Effect Transistor

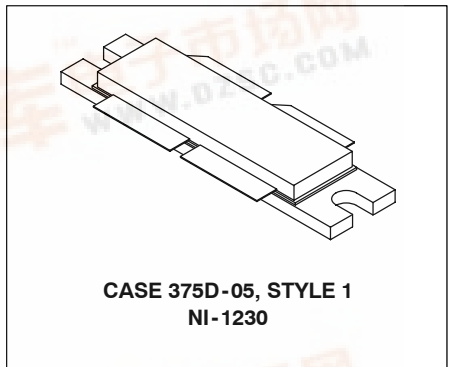
## N-Channel Enhancement-Mode Lateral MOSFET

Designed for N-CDMA base station applications with frequencies from 2600 to 2700 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN - PCS/cellular radio and WLL applications.

- Typical Single-Carrier N-CDMA Performance:  $V_{DD} = 28$  Volts,  $I_{DQ} = 2 \times 900$  mA,  $P_{out} = 35$  Watts Avg., Full Frequency Band, IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz. Peak/Avg. = 9.8 dB @ 0.01% Probability on CCDF.  
Power Gain — 14.6 dB  
Drain Efficiency — 22.6%  
ACPR @ 885 kHz Offset — -47.8 dBc @ 30 kHz Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 2700 MHz, 160 Watts CW Output Power
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched, Controlled Q, for Ease of Use
- Qualified Up to a Maximum of 32  $V_{DD}$  Operation
- Integrated ESD Protection
- Lower Thermal Resistance Package
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- Low Gold Plating Thickness on Leads, 40 $\mu$ ” Nominal.
- In Tape and Reel. R6 Suffix = 150 Units per 56 mm, 13 inch Reel.



**2700 MHz, 35 W AVG., 28 V  
SINGLE N-CDMA  
LATERAL N-CHANNEL  
RF POWER MOSFET**



**Table 1. Maximum Ratings**

Rating	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	-0.5, +68	Vdc
Gate-Source Voltage	$V_{GS}$	-0.5, +12	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25 $^\circ\text{C}$	$P_D$	603 3.45	W W/ $^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to +150	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	200	$^\circ\text{C}$
CW Operation	CW	160	W

**Table 2. Thermal Characteristics**

Characteristic	Symbol	Value (1,2)	Unit
Thermal Resistance, Junction to Case Case Temperature 79 $^\circ\text{C}$ , 160 W CW Case Temperature 71 $^\circ\text{C}$ , 35 W CW	$R_{\theta JC}$	0.29 0.31	$^\circ\text{C}/\text{W}$

1. MTTF calculator available at <http://www.freescale.com/rf>. Select Tools/Software/Application Software/Calculators to access the MTTF calculators by product.
2. Refer to AN1955/D, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

**NOTE - CAUTION** - MOS devices are susceptible to damage from electrostatic charge. Reasonable precautions in handling and packaging MOS devices should be observed.



**Table 3. ESD Protection Characteristics**

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	III (Minimum)

**Table 4. Electrical Characteristics** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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**Off Characteristics**

Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 68\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	10	$\mu\text{A}$
Zero Gate Voltage Drain Leakage Current ( $V_{DS} = 28\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	—	—	1	$\mu\text{A}$
Gate-Source Leakage Current ( $V_{GS} = 5\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	—	—	1	$\mu\text{A}$

**On Characteristics**

Gate Threshold Voltage ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 250\ \mu\text{A}$ )	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ( $V_{DS} = 28\text{ Vdc}$ , $I_D = 900\ \text{mA}$ )	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ( $V_{GS} = 10\text{ Vdc}$ , $I_D = 2.2\ \text{A}$ )	$V_{DS(on)}$	—	0.21	0.3	Vdc
Forward Transconductance ( $V_{DS} = 10\text{ Vdc}$ , $I_D = 2\ \text{A}$ )	$g_{fs}$	—	5.3	—	S

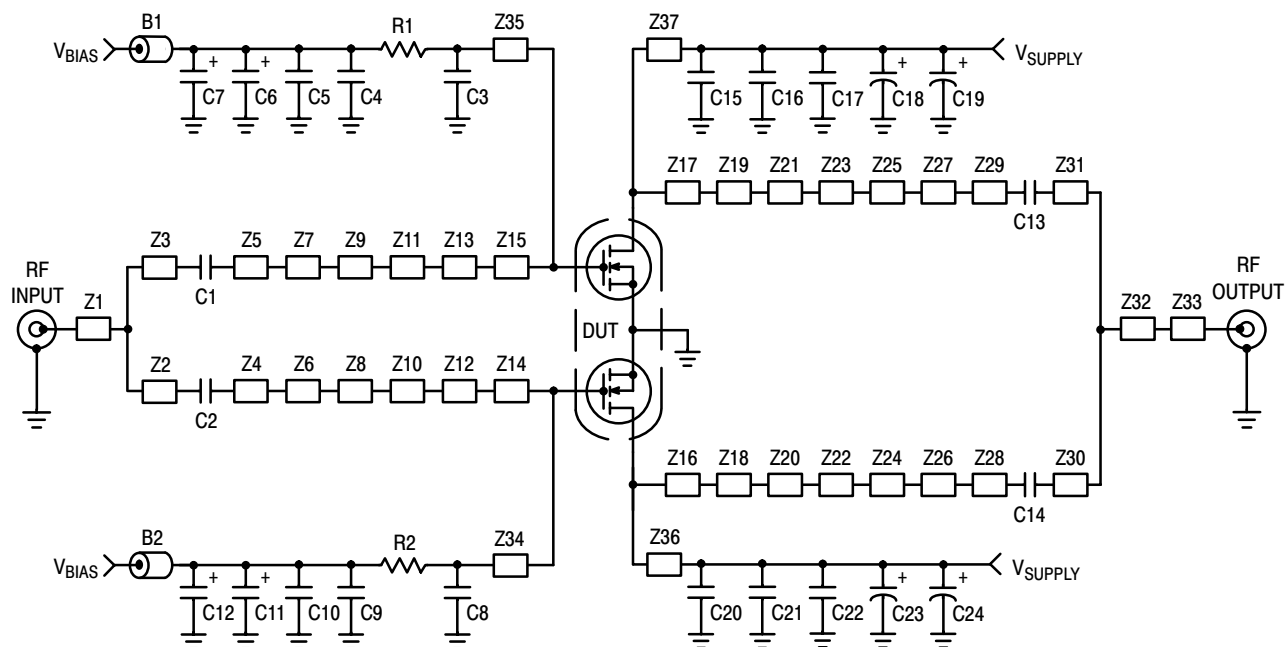
**Dynamic Characteristics** <sup>(1)</sup>

Reverse Transfer Capacitance ( $V_{DS} = 28\text{ Vdc} \pm 30\ \text{mV(rms)}$ ac @ 1 MHz, $V_{GS} = 0\text{ Vdc}$ )	$C_{rss}$	—	2.8	—	pF
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**Functional Tests** (In Freescale Test Fixture, 50 ohm system)  $V_{DD} = 28\text{ Vdc}$ ,  $I_{DQ} = 2 \times 900\ \text{mA}$ ,  $P_{out} = 35\ \text{W Avg.}$  N-CDMA,  $f = 2630$  and  $2660\ \text{MHz}$ , Single-Carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carrier. ACPR measured in 30 kHz Channel Bandwidth @  $\pm 885\ \text{kHz}$  Offset. Peak/Avg. = 9.8 dB @ 0.01% Probability on CCDF

Power Gain	$G_{ps}$	13	14.6	16	dB
Drain Efficiency	$\eta_D$	20	22.6	—	%
Adjacent Channel Power Ratio	ACPR	—	-47.8	-45	dBc
Input Return Loss	IRL	—	-13	-9	dB

1. Part is internally matched both on input and output.

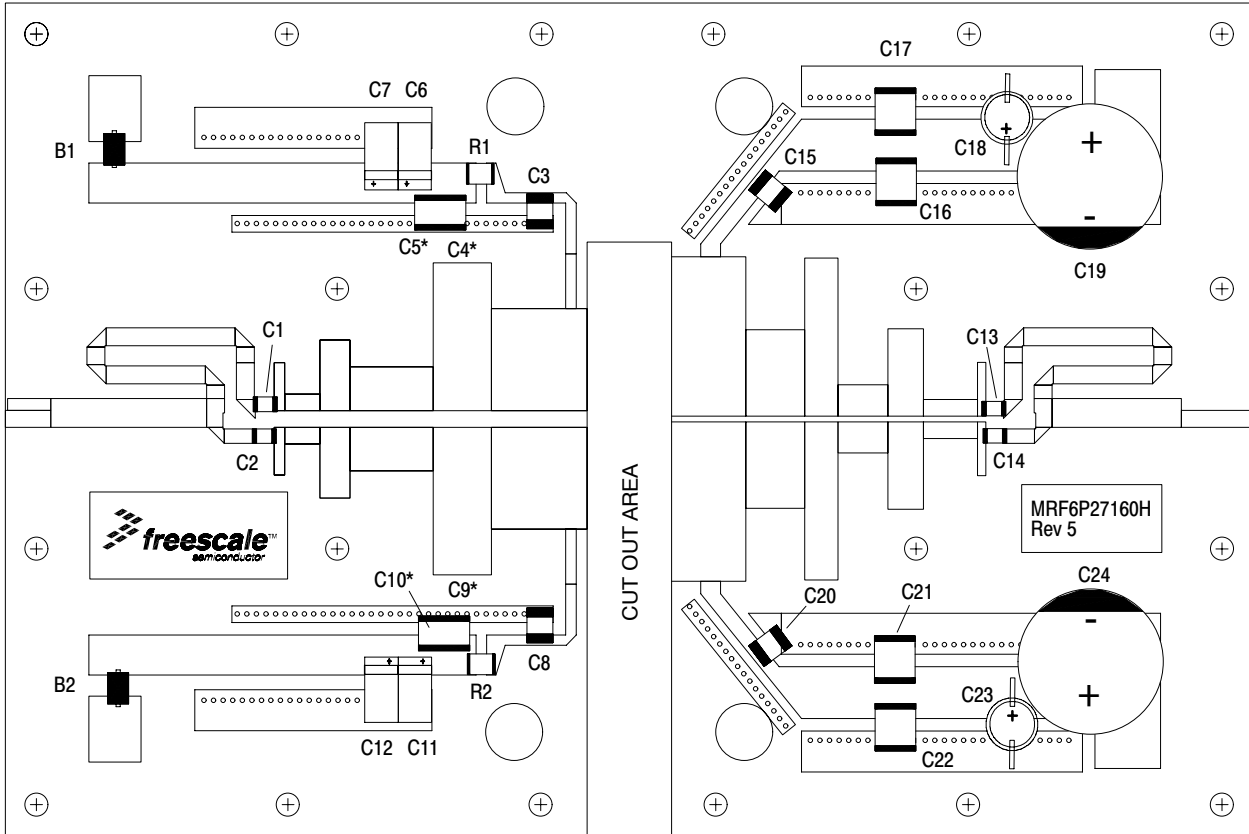


Z1	1.011" x 0.139" Microstrip	Z20, Z21	0.160" x 0.760" Microstrip
Z2, Z31	0.150" x 0.070" Microstrip	Z22, Z23	0.240" x 0.150" Microstrip
Z3, Z30	1.500" x 0.086" Microstrip	Z24, Z25	0.170" x 0.420" Microstrip
Z4, Z5	0.050" x 0.230" Microstrip	Z26, Z27	0.260" x 0.080" Microstrip
Z6, Z7	0.170" x 0.080" Microstrip	Z28, Z29	0.040" x 0.258" Microstrip
Z8, Z9	0.144" x 0.340" Microstrip	Z32	0.622" x 0.139" Microstrip
Z10, Z11	0.400" x 0.210" Microstrip	Z33	0.346" x 0.081" Microstrip
Z12, Z13	0.280" x 0.710" Microstrip	Z34, Z35	0.801" x 0.050" Microstrip
Z14, Z15	0.461" x 0.490" Microstrip	Z36, Z37	0.460" x 0.095" Microstrip
Z16, Z17	0.357" x 0.766" Microstrip	PCB	Arlon GX-0300-5022, 0.030", $\epsilon_r = 2.5$
Z18, Z19	0.284" x 0.415" Microstrip		

**Figure 1. MRF6P27160HR6 Test Circuit Schematic**

**Table 5. MRF6P27160HR6 Test Circuit Component Designations and Values**

Part	Description	Part Number	Manufacturer
B1, B2	Beads, Surface Mount	2743019447	Fair-Rite
C1, C2	5.6 pF Chip Capacitors	100B5R6CP500X	ATC
C3, C8, C15, C20	3.3 pF Chip Capacitors	100B3R3CP500X	ATC
C4, C9	0.01 $\mu$ F Chip Capacitors (1825)	C1825C103J1RAC	Kemet
C5, C10	2.2 $\mu$ F, 50 V Chip Capacitors (1825)	C1825C225J5RAC	Kemet
C6, C11	22 $\mu$ F, 25 V Tantalum Chip Capacitors	ECS-T1ED226R	Panasonic TE Series
C7, C12	47 $\mu$ F, 16 V Tantalum Chip Capacitors	T491D476K016AS	Kemet
C13, C14	4.3 pF Chip Capacitors	100B4R3CP500X	ATC
C16, C17, C21, C22	10 $\mu$ F, 50 V Chip Capacitors (2220)	GRM55DR61H106KA88B	Murata
C18, C23	47 $\mu$ F, 50 V Electrolytic Capacitors	MVK50VC47RM8X10TP	Nippon
C19, C24	330 $\mu$ F, 63 V Electrolytic Capacitors	NACZF331M63V	Nippon
R1, R2	3.3 $\Omega$ , 1/4 W Chip Resistors (1210)	ERJ-14YJ3R3U	Dale/Vishay



\*Stacked

**Figure 2. MRF6P27160HR6 Test Circuit Component Layout**

### TYPICAL CHARACTERISTICS

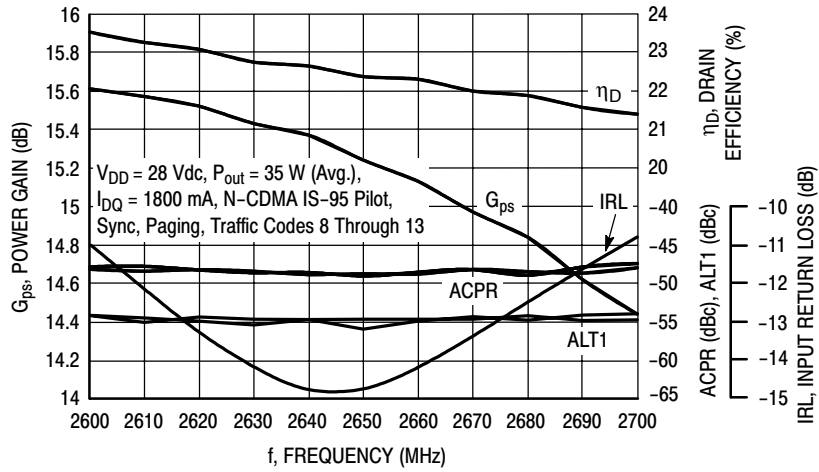


Figure 3. Single-Carrier N-CDMA Broadband Performance @  $P_{out} = 35$  Watts Avg.

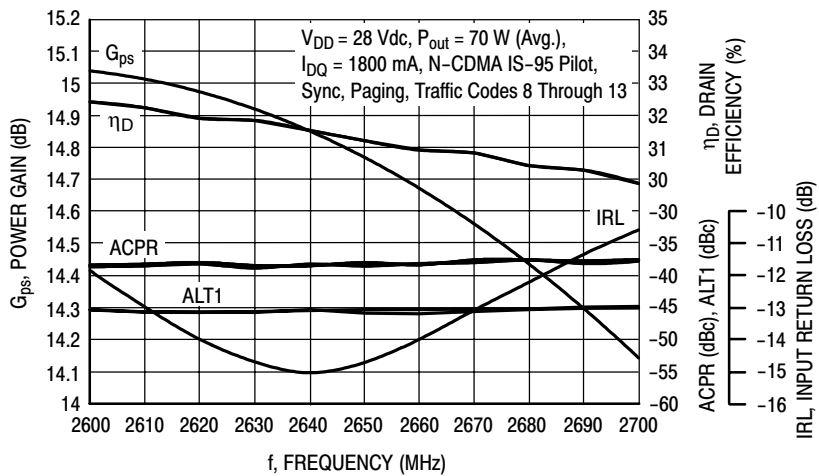


Figure 4. Single-Carrier N-CDMA Broadband Performance @  $P_{out} = 70$  Watts Avg.

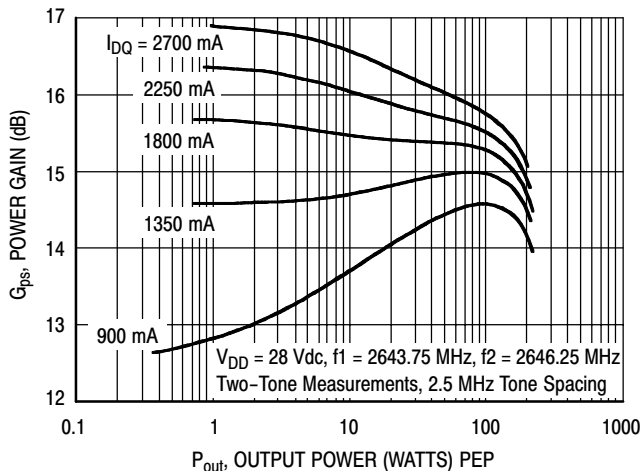


Figure 5. Two-Tone Power Gain versus Output Power

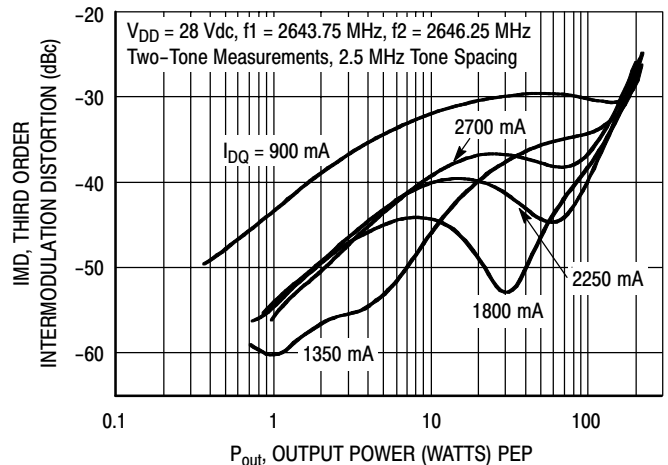


Figure 6. Third Order Intermodulation Distortion versus Output Power

## TYPICAL CHARACTERISTICS

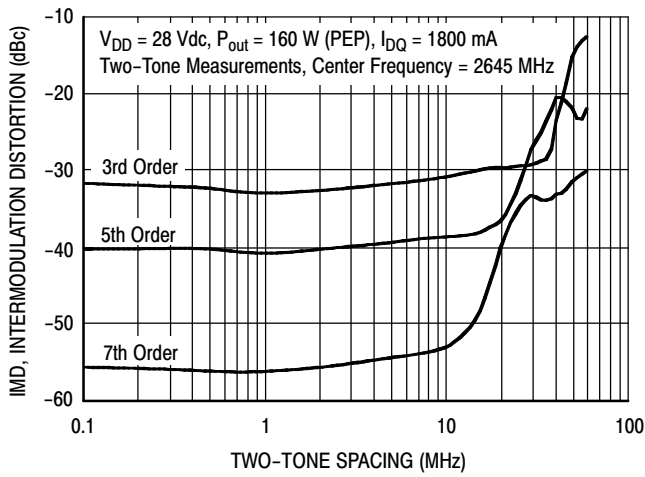


Figure 7. Intermodulation Distortion Products versus Tone Spacing

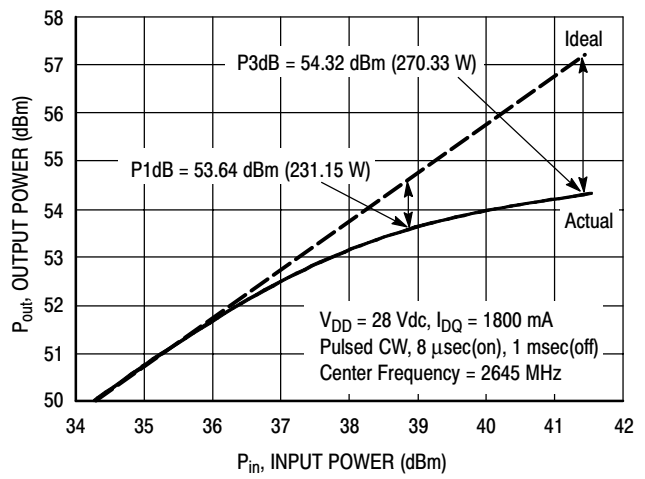


Figure 8. Pulse CW Output Power versus Input Power

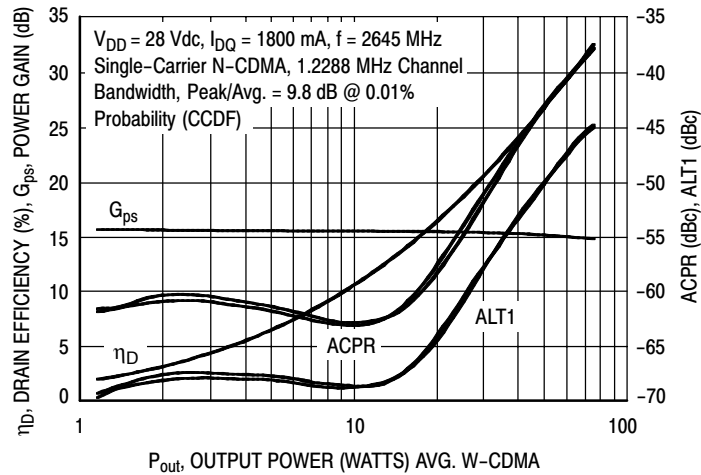


Figure 9. Single-Carrier N-CDMA ACPR, ALT1, Power Gain and Drain Efficiency versus Output Power

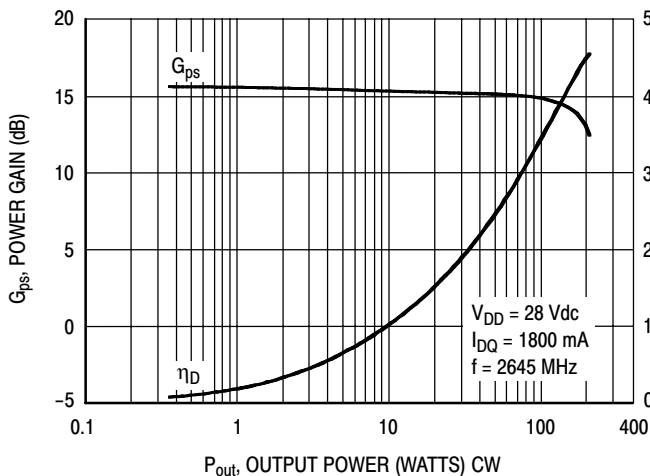


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

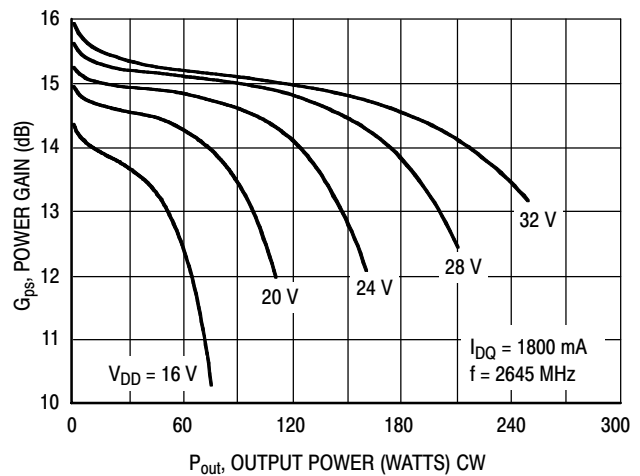
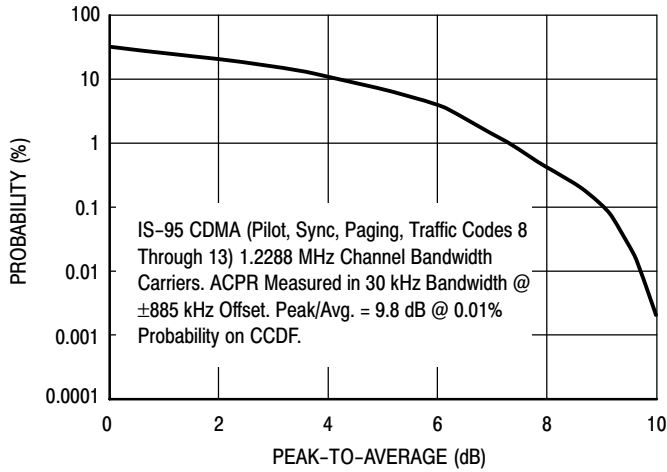
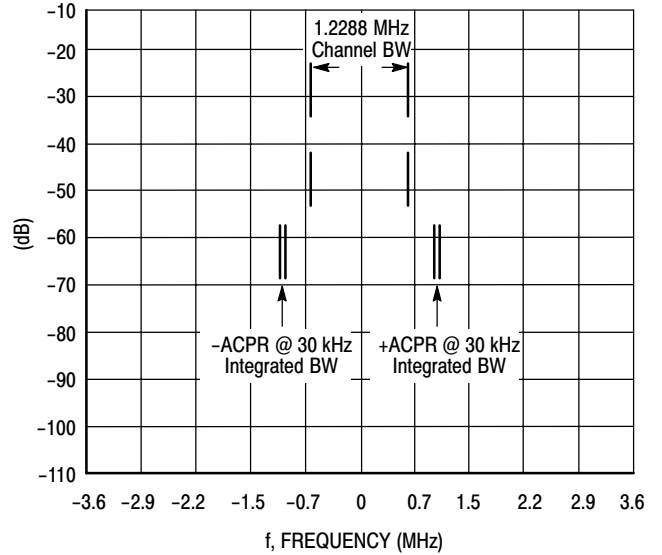


Figure 11. Power Gain versus Output Power

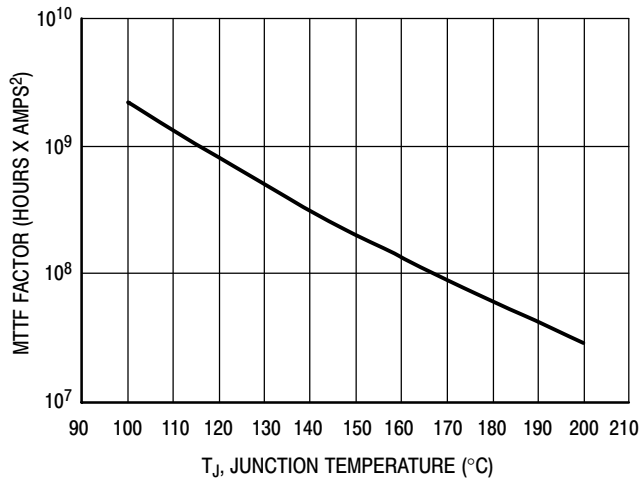
## TYPICAL CHARACTERISTICS N-CDMA TEST SIGNAL



**Figure 12. Single-Carrier CCDF N-CDMA**

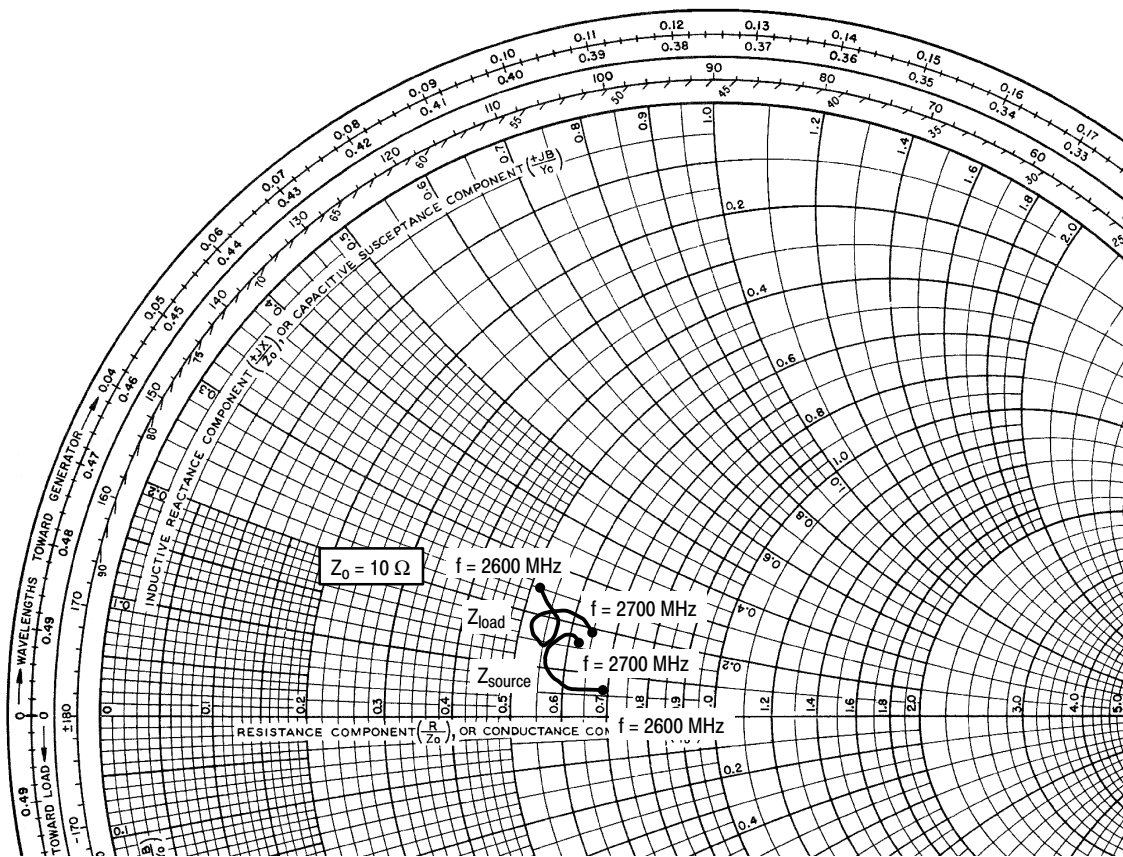


**Figure 13. Single-Carrier N-CDMA Spectrum**



This above graph displays calculated MTTF in hours x ampere<sup>2</sup> drain current. Life tests at elevated temperatures have correlated to better than  $\pm 10\%$  of the theoretical prediction for metal failure. Divide MTTF factor by  $I_D^2$  for MTTF in a particular application.

**Figure 14. MTTF Factor versus Junction Temperature**



$V_{DD} = 28 \text{ Vdc}$ ,  $I_{DQ} = 1800 \text{ mA}$ ,  $P_{out} = 35 \text{ W Avg.}$

f MHz	$Z_{source}$ $\Omega$	$Z_{load}$ $\Omega$
2600	$6.90 + j0.61$	$5.24 + j2.46$
2610	$6.85 + j0.63$	$5.69 + j2.04$
2620	$6.76 + j0.59$	$5.71 + j1.59$
2630	$6.50 + j0.59$	$5.62 + j1.48$
2640	$6.13 + j0.56$	$5.45 + j1.42$
2645	$5.95 + j0.69$	$5.38 + j1.49$
2650	$5.81 + j0.83$	$5.31 + j1.58$
2660	$5.61 + j1.15$	$5.24 + j1.81$
2670	$5.69 + j1.48$	$5.45 + j2.09$
2680	$5.91 + j1.67$	$5.84 + j2.22$
2690	$6.12 + j1.68$	$6.22 + j2.12$
2700	$6.17 + j1.60$	$6.49 + j1.92$

$Z_{source}$  = Test circuit impedance as measured from gate to gate, balanced configuration.

$Z_{load}$  = Test circuit impedance as measured from drain to drain, balanced configuration.

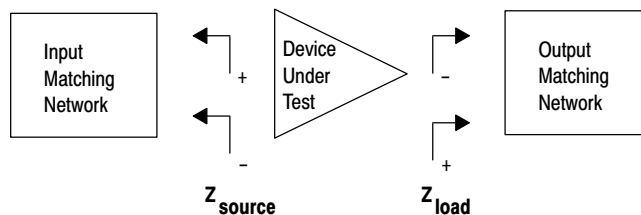


Figure 15. Series Equivalent Source and Load Impedance



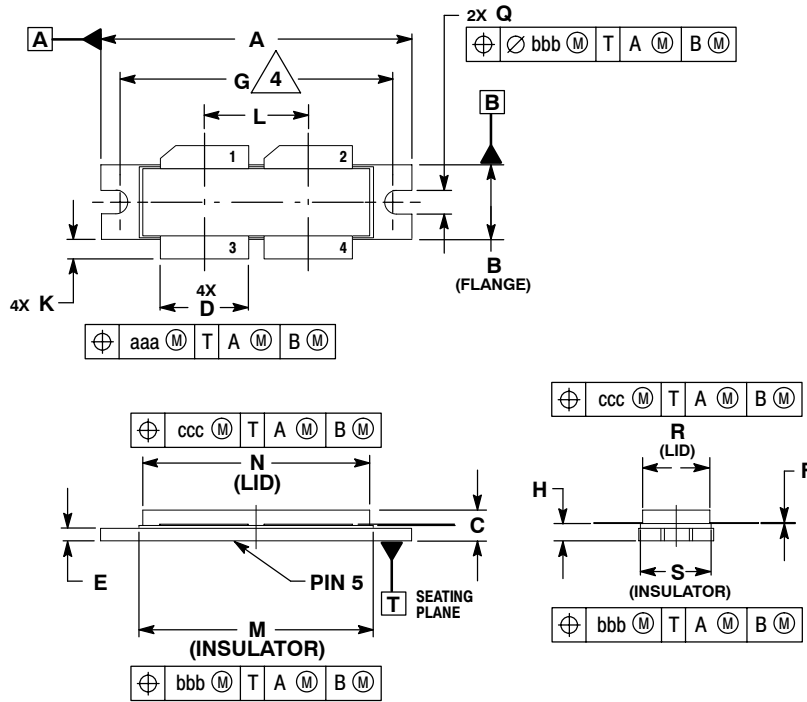


# NOTES



## NOTES

## PACKAGE DIMENSIONS



- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
  4. RECOMMENDED BOLT CENTER DIMENSION OF 1.52 (38.61) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.615	1.625	41.02	41.28
B	0.395	0.405	10.03	10.29
C	0.150	0.200	3.81	5.08
D	0.455	0.465	11.56	11.81
E	0.062	0.066	1.57	1.68
F	0.004	0.007	0.10	0.18
G	1.400 BSC		35.56 BSC	
H	0.082	0.090	2.08	2.29
K	0.117	0.137	2.97	3.48
L	0.540 BSC		13.72 BSC	
M	1.219	1.241	30.96	31.52
N	1.218	1.242	30.94	31.55
Q	0.120	0.130	3.05	3.30
R	0.355	0.365	9.01	9.27
S	0.365	0.375	9.27	9.53
aaa	0.013 REF		0.33 REF	
bbb	0.010 REF		0.25 REF	
ccc	0.020 REF		0.51 REF	

- STYLE 1:
- PIN 1. DRAIN
  2. DRAIN
  3. GATE
  4. GATE
  5. SOURCE

**CASE 375D-05  
ISSUE D  
NI-1230**

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Freescale Halbleiter Deutschland GmbH  
Technical Information Center  
Schatzbogen 7  
81829 Muenchen, Germany  
+44 1296 380 456 (English)  
+46 8 52200080 (English)  
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[support@freescale.com](mailto:support@freescale.com)

### **Japan:**

Freescale Semiconductor Japan Ltd.  
Headquarters  
ARCO Tower 15F  
1-8-1, Shimo-Meguro, Meguro-ku,  
Tokyo 153-0064  
Japan  
0120 191014 or +81 3 5437 9125  
[support.japan@freescale.com](mailto:support.japan@freescale.com)

### **Asia/Pacific:**

Freescale Semiconductor Hong Kong Ltd.  
Technical Information Center  
2 Dai King Street  
Tai Po Industrial Estate  
Tai Po, N.T., Hong Kong  
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